

2SK995

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Silicon N-channel Power F-MOS FET

■ Features

- Low ON resistance $R_{DS(on)} : R_{DS(on)} = 1.2\Omega$ (typ.)
- High switching rate : $t_r = 65\text{ns}$ (typ.)
- No secondary breakdown
- High breakdown voltage, large power
- Fast recovery diode (FRD) built-in

■ Application

- No contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching power source

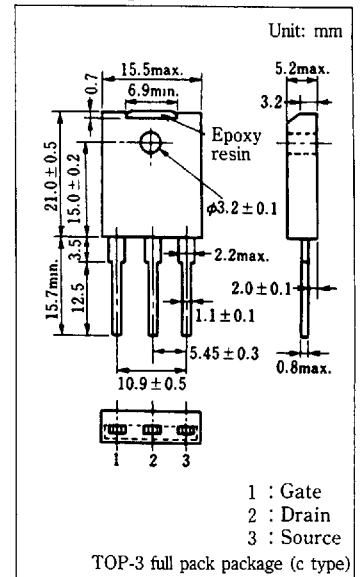
■ Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$)

| Item | Symbol | Value | Unit |
|----------------------|--------------------------|-----------------|------------------|
| Drain-source voltage | V_{DSS} | 550 | V |
| Gate-source voltage | V_{GSS} | ± 20 | V |
| Drain current | DC | I_D | 5 |
| | Peak to-peak value | I_{DP} | 10 |
| Power dissipation | $T_c = 25^\circ\text{C}$ | P_D | 60 |
| | $T_a = 25^\circ\text{C}$ | | 3.0 |
| Channel temperature | T_{ch} | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | $-55 \sim +150$ | $^\circ\text{C}$ |

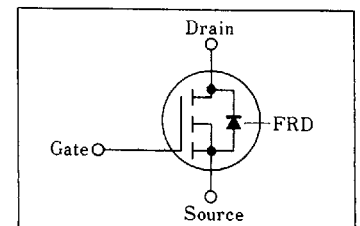
■ Electrical Characteristics ($T_c = 25^\circ\text{C}$)

| Item | Symbol | Condition | min. | typ. | max. | Unit | |
|------------------------------|-------------------|--|------------------------------------|------|---------|---------------|----|
| Drain current | I_{DSS} | $V_{DS} = 440\text{V}, V_{GS} = 0$ | | | 0.1 | mA | |
| Gate-source current | I_{GSS} | $V_{GS} = \pm 20\text{V}, V_{DS} = 0$ | | | ± 1 | μA | |
| Drain-source voltage | V_{DSS} | $I_D = 1\text{mA}, V_{GS} = 0$ | 550 | | | V | |
| Gate threshold voltage | V_{th} | $V_{DS} = 25\text{V}, I_D = 1\text{mA}$ | 1 | | 5 | V | |
| Drain-source ON resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{V}, I_D = 3\text{A}$ | | 1.2 | 1.8 | Ω | |
| Forward transfer admittance | $ Y_{fs} $ | $V_{DS} = 25\text{V}, I_D = 3\text{A}$ | 3.5 | 5.5 | | S | |
| Input capacitance | C_{iss} | $V_{DS} = 20\text{V}, V_{GS} = 0, f = 1\text{MHz}$ | | 1500 | | pF | |
| Output capacitance | C_{oss} | | | | 160 | | pF |
| Reverse transfer capacitance | C_{rss} | | | | 50 | | pF |
| Turn-on time | t_{on} | $V_{GS} = 10\text{V}, I_D = 3\text{A}$ | | 50 | | ns | |
| Fall time | t_f | | | | 65 | | ns |
| Delay time | $t_d(\text{off})$ | $V_{DD} = 150\text{V}, R_L = 50\Omega$ | | 300 | | ns | |
| Reverse time | t_{rr} | | $I_F = 1\text{A}, I_R = 1\text{A}$ | | 200 | 400 | ns |

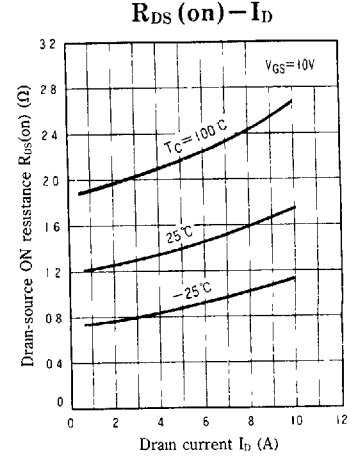
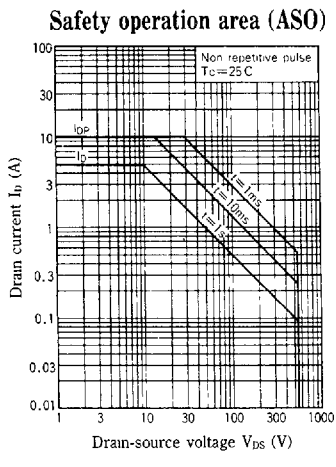
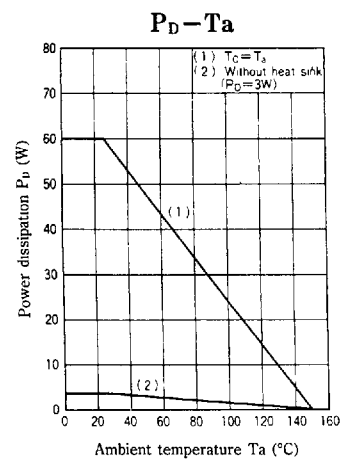
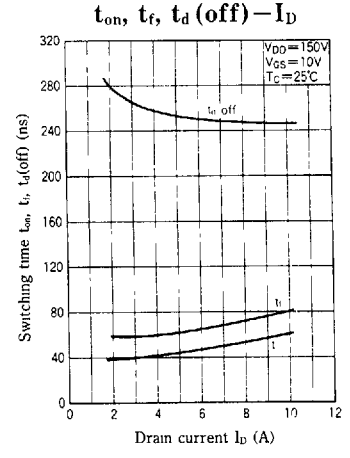
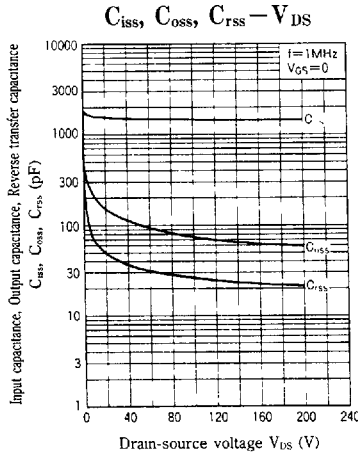
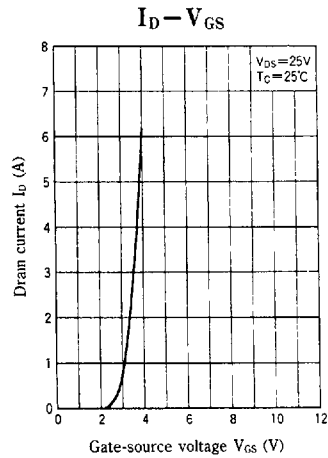
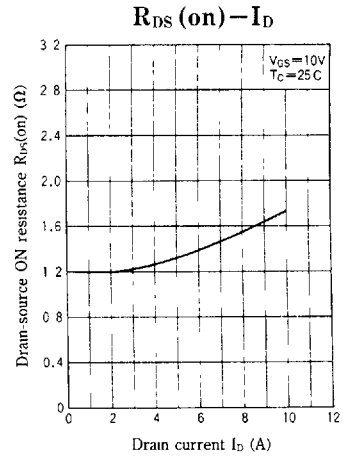
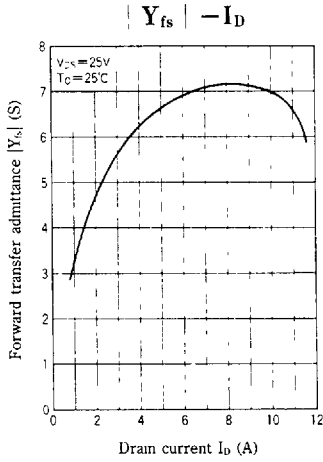
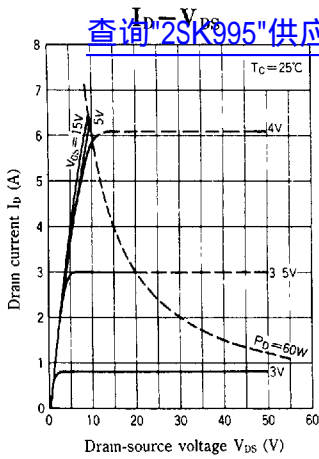
■ Package Dimensions



■ Inner Circuit



$I_D - V_{DS}$
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